

Sheet 1 of 1

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|--------------------|-------------------|------------|
| Atty. Docket No.   | JAN 08 2009       | Serial No. |
| <b>2490-31</b>     | <b>10/585,324</b> |            |
| Applicant          | DUNKLEY ET AL.    |            |
| Filing Date        | TC/A.U.           |            |
| September 26, 2006 | 2812              |            |

## **INFORMATION DISCLOSURE CITATION**

(Use several sheets if necessary)

## **U.S. PATENT DOCUMENTS**

## **FOREIGN PATENT DOCUMENTS**

**OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)**

Properties of Porous Silicon, edited by Leigh Canhan, DERA, Malvern, UK, Published by INSPEC, The Institution of Electrical Engineers, London, United Kingdom, ISBN 085296 932 5, Halimaoui, "1.2 Porous Silicon Formation by Anodisation", pages 12-19; 1997.

\*Examiner \_\_\_\_\_ Date Considered \_\_\_\_\_

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.